

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device of the present invention includes: a semiconductor substrate; a memory cell capacitor for storing data, including a first electrode provided above the semiconductor substrate, a capacitance insulating film formed on the first electrode, and a second electrode provided on the capacitance insulating film; a step reducing film covering an upper surface and a side surface of the memory cell capacitor; and an overlying hydrogen barrier film covering the step reducing film.

204270-012402
1053693-012402